

*Subs Cont*  
(d) generating a plasma of said etching gas at a second power level in said chamber and contacting said integrated circuit substrate with said second power level plasma for a second predetermined time, wherein said second power level plasma is a higher power plasma than said first power level plasma, and wherein said substrate has a CD loss decreased compared to the CD loss of a substrate formed by a method comprising said steps (a), (b) and (c) but not step (d).  
*B' End Subs*

93. (New) The integrated circuit substrate of claim 92, wherein said CD loss is decreased by about 400 Angstroms.

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